

***Listing of the Claims:***

1. (Currently Amended) A wiring layer structure connected to a first electrode of a ferroelectric capacitor having first and second electrodes, comprising:
  - a main wiring layer including a first material; and
  - a coating layer including a first coating part provided between said main wiring layer and said first electrode, a second coating part provided on the top surface of said main wiring layer, and a third coating part ~~covering~~provided on side faces of said main wiring layer;wherein said first material reacts with a substance to produce a reducing agent, said substance being infiltrated from the outside to this main wiring layer, and said coating layer is conductive and comprises a second material for preventing the infiltration of said substance into said main wiring layer.
2. (Original) The wiring layer structure according to Claim 1, wherein said first material is aluminum (Al).
3. (Original) The wiring layer structure according to Claim 1, wherein said second material is titanium nitride (TiN).
4. (Original) The wiring layer structure according to Claim 1, wherein said second material is titanium (Ti).
5. (Original) The wiring layer structure according to Claim 1, wherein said second material is titanium nitride (TiN) and titanium (Ti).
6. (Canceled)

7. (Previously Amended) The wiring layer structure according to Claim 1, wherein said first, second, and third coating parts are titanium nitride (TiN) films.
8. (Previously Amended) The wiring layer structure according to Claim 1, wherein said first and third coating parts are titanium nitride (TiN) films, and said second coating part is a built-up film composed of a titanium (Ti) film and a titanium nitride (TiN) film.
9. (Previously Amended) The wiring layer structure according to Claim 1, wherein said first coating part is a titanium nitride (TiN) film, and wherein said second and third coating parts are built-up films composed of a titanium (Ti) film and a titanium nitride (TiN) film.
10. (Previously Amended) The wiring layer structure according to Claim 1, wherein said first coating part is a titanium nitride (TiN) sputtering film, and said second and third coating parts are TiN-CVD films.
11. (Previously Amended) The wiring layer structure according to Claim 1, wherein said first and second coating parts are TiN-sputtering films, and said third coating part is a TiN-CVD film.
12. (Previously Amended) The wiring layer structure according to Claim 1, wherein said first coating part is a TiN-sputtering film, said second coating part is a built-up film composed of a Ti-sputtering film and a TiN-sputtering film, and said third coating part is a TiN-CVD film.
13. (Previously Amended) The wiring layer structure according to Claim 1, wherein said first coating part is a TiN-sputtering film, said second coating part is a built-up film formed from a Ti-sputtering film and a TiN-sputtering film, and said third coating part is a built-up film formed from a Ti-CVD film and a TiN-CVD film.

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14. (Original) The wiring layer structure according to Claim 1, wherein said substance infiltrating from the outside is either water ( $H_2O$ ) or hydrogen ( $H_2$ ).
15. (Original) The wiring layer structure according to Claim 1, wherein said reducing agent is either a hydrogen radical ( $H^*$ ) or hydrogen ( $H_2$ ).